



REPLACEMENT SHEET

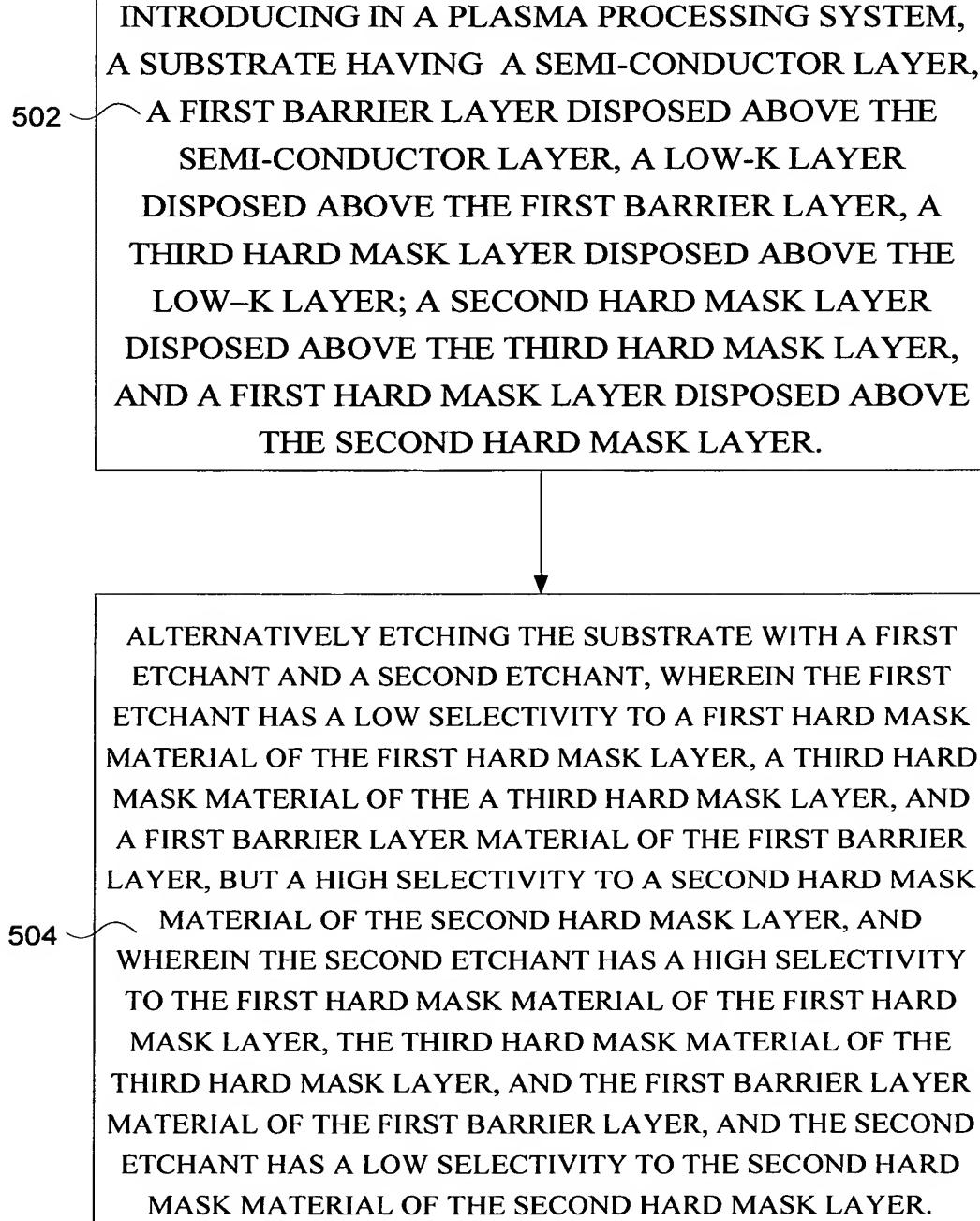


FIG. 5A



REPLACEMENT SHEET

- INTRODUCING IN A PLASMA PROCESSING SYSTEM,  
A SUBSTRATE HAVING A SEMI-CONDUCTOR LAYER,  
A FIRST BARRIER LAYER DISPOSED ABOVE THE  
506 SEMI-CONDUCTOR LAYER, A LOW-K LAYER  
DISPOSED ABOVE THE FIRST BARRIER LAYER, A  
SECOND BARRIER LAYER DISPOSED ABOVE THE  
LOW-K LAYER, A THIRD HARD MASK LAYER  
DISPOSED ABOVE THE SECOND BARRIER LAYER, A  
SECOND HARD MASK LAYER DISPOSED ABOVE THE  
THIRD HARD MASK LAYER, AND A FIRST HARD  
MASK LAYER DISPOSED ABOVE THE SECOND HARD  
MASK LAYER.
- ALTERNATIVELY ETCHING THE SUBSTRATE WITH A FIRST  
ETCHANT AND A SECOND ETCCHANT, WHEREIN THE FIRST  
ETCHANT HAS A LOW SELECTIVITY TO A FIRST HARD MASK  
MATERIAL OF THE FIRST HARD MASK LAYER, A THIRD HARD  
MASK MATERIAL OF THE A THIRD HARD MASK LAYER, AND  
A FIRST BARRIER LAYER MATERIAL OF THE FIRST BARRIER  
LAYER, BUT A HIGH SELECTIVITY TO A SECOND HARD MASK  
508 MATERIAL OF THE SECOND HARD MASK LAYER, AND  
WHEREIN THE SECOND ETCCHANT HAS A HIGH SELECTIVITY  
TO THE FIRST HARD MASK MATERIAL OF THE FIRST HARD  
MASK LAYER, THE THIRD HARD MASK MATERIAL OF THE  
THIRD HARD MASK LAYER, AND THE FIRST BARRIER LAYER  
MATERIAL OF THE FIRST BARRIER LAYER, AND THE SECOND  
ETCHANT HAS A LOW SELECTIVITY TO THE SECOND HARD MASK  
MASK MATERIAL OF THE SECOND HARD MASK LAYER AND  
THE SECOND BARRIER LAYER.

FIG. 5B